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A Camera with adaptive Photoreceptors in analog CMOS Technology

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ABSTRACT

A system of adaptive photoreceptors has been designed and built in a standard CMOS process. The mechanism of adaptation is based on an analog feedback circuit modelled after the biological example. The system exhibits a large dynamic range of approximately 7 orders of magnitude in light intensity and a pronounced capability to detect moving objects. Simulations and measurements with single adaptive receptors as well as first experiences with a camera system are presented.

1 CONCEPT

The *Complementary Metal Oxide Silicon (short : CMOS)* technology plays a major role for mass production of integrated circuits. The availability of basic circuit elements like diodes and transistors suggests to use the intrinsic photoelectric effect in the depletion zone of CMOS structures for light detection. At the same time the possibilities for further signal processing on the same silicon wafer can be used. This is the basic idea of CMOS photoreceptors (*Vision Chips*). Apart from the integration of sensor elements and signal processing single CMOS photoreceptors are characterised by a huge dynamic range of 1 : 1 million or more. This performance comes close to the biological model and is far better than that of conventional CCD systems. In practical applications however, the use of the large dynamic range is difficult. A linear transfer of many orders of magnitude in incident illumination requires an unrealistic range of output voltages. A way out of this problem also realised in biological systems is a logarithmic compression of the output signal. Such a compression permits the acquisition of scenes with extremely high contrasts. The obvious disadvantage of such a flat logarithmic transfer curve is that pictures of normal scenes without extreme contrasts appear essentially grey. Biological system on the other hand can handle large and small input contrast because of their capability of adaptation. In the language of analog electronics an adaptive photoreceptor represents a bandpass filter. The response to static or very low frequency input signals can be described by a low gain logarithmic transfer characteristics (*static response*). Rapidly changing signals see a much higher logarithmic gain (*transient response*). The biological system adapts with time constants of typically seconds (minutes or more for dark adaptation). The bandpass characteristics causes a prounounced capability for motion detection. This paper describes the electronic realisation of a biologically motivated adaptive photoreceptor based on an analog feedback circuit. The system and its properties are described in more detail in.[1]

2 BIOLOGICAL MODEL

Fig. 1 shows the measured membrane potential of a turtle cone (red sensitive) as measured by Normann and Perlman.[2] The static response of this system is characterised by a rather flat logarithmic slope of about 1.8 mV/decade. The steep curves describe the response to rapid changes of incident illumination. Their slope is much higher (about 9.5 mV/decade).

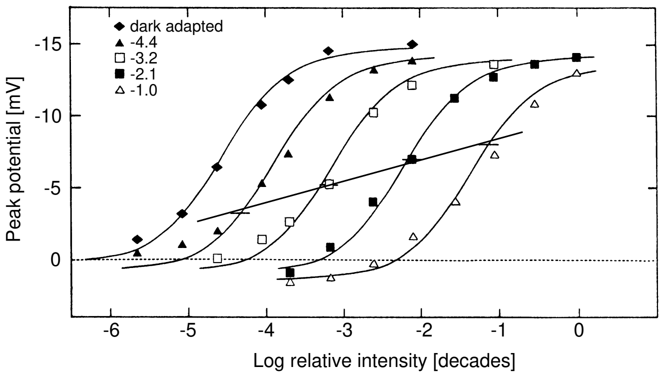

Figure 1: Response curves of red sensitive cones in the turtle retina.[2] The measured membrane potential (relative to the dark potential represented by the dotted line) is plotted as a function of the intensity of the incoming light. The 0. decade corresponds to an intensity of about 20 W/m^2. The full straight line describes the static response of the system two minutes after it was first exposed to a constant illumination. The measured points connected by the steeper lines show the response to light pulses of 0.5 s duration. The light pulses rise from a given lower intensity written next to the symbol table in the figure.

This adaptive behaviour allows the receptor to operate with high logarithmic gain over a wide range of light intensities without suffering from saturation. The output signal mostly represents the actual changes in incident illumination. Static signals are highly suppressed. The high gain response to transient signals causes increased sensitivity to moving objects as well as an enhancement of edges since moving objects show changes in intensity predomionantly at their edges.

3 TECHNICAL REALISATION

3.1 Electronic realisation of an adaptive pixel

The circuit for the adaptive photoreceptor described here closely follows the suggestion by T. Delbrück and C. A. Mead.[3] The circuit is shown in Fig. 2. Basically an internal model makes a prediction about the level of the input signal. The output signal is then generated from a comparison between the prediction and the actual input. Finally the circuit corrects its internal model in order to improve the prediction.

The input stage of the receptor consists of a reverse biased photodiode and a feedback transistor M_{fb}. Typical incident illuminations correspond to diode photocurrents in the range of pA to nA. This causes the feedback transistor M_{fb} to operate in the subthreshold region. As a consequence the source voltage V_s is proportional to the logarithm of the photocurrent I_{ph}. The gate-source voltage between the potentials V_{cap} and V_s settles to a value required to deliver the current needed by the diode. The voltage V_{cap} is stored on the capacitance C_1 and acts as a model for the input intensity.

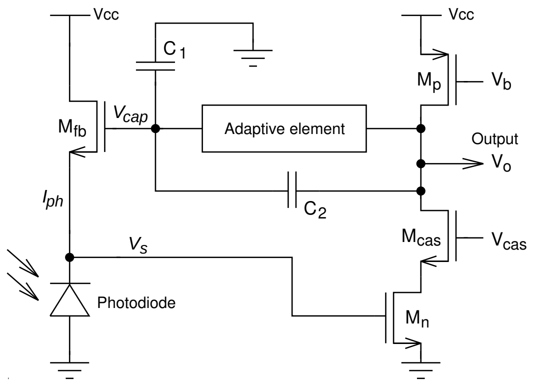

Figure 2: Circuit of the adaptive photoreceptor.

The comparison between input signal and model prediction is carried out by the inverting amplifier formed by the transistors M_p und M_n. The voltage V_s regulates the current flowing through M_n. The current through the p-MOS-transistor M_p is set by the external bias voltage V_b. The voltage gain v_{amp} is given by the ratio of the output impedance of the amplifier and the impedance of M_n. The gain value is determined by the lengths of the transistors. Typical values are in the range of 1000. The additional cascode transistor M_{cas} increases the drain impedance of M_n and leads to a further increase of the voltage gain. In addition the amplifier gets faster. M_{cas} protects the drain of M_n such that the gate-drain capacitance of M_n is only exposed to small voltage changes. In consequence the input voltage V_s needs to drive only a small capacitance. The output signal V_o is fed back over the *adaptive element* and a capacitive divider formed by C_1 und C_2 to the gate of the feedback transistor M_{fb}.

The adaptive element consists of a p-MOS-transistor with a short circuit between drain and gate and a parasitc bipolar pnp transistor with two collectors. One collector ist connected to the base and the other is formed by the subtrate which is on ground potential. The system basically acts like two parallel connected diodes with opposite polarity. Independent of its direction the current rises exponentially as a function of the applied voltage. For small voltages the system corresponds to an extremely large resistor with a value of typically 10^{12} Ω. This value is essential to obtain a long RC time constant with the small capacitors available in VLSI technology. The realisation of the adaptive element for this project follows closely the description in.[3]

The adaptation mechanism works in the following way : A small increase of the photocurrent I_{ph} tries to pull down the voltage V_s. The output voltage V_o reacts with an increase given by the voltage gain v_{amp}. At the same time the output voltage is fed back through the capacitive divider to the gate of the feedback transistor M_{fb}. In consequence the voltages V_{cap} and V_s move up. Hence the the feedback mechanism acts to compensate the initial perturbation such that V_s is held almost constant. For slow changes the gain of the receptor is small because the feedback takes place across the large but finite resistor formed by the adaptive element. For rapid changes however, no current can flow across the adaptive element and the changes are transmitted to the gate of M_{fb} via the capacitive divider. This causes a damping of the feedback signal and hence requires a larger reaction of the output voltage V_o in order to keep V_s at a constant value. The gain of the circuit to transient signals is given by the ratio of capacitances in the divider. The larger C_1 relative to C_2 the larger the gain is.

3.2 CMOS LAYOUT

Based on the adaptive circuit described in the previous chapter a CMOS chip has been designed and produced. The chip contains single adaptive photoreceptors (pixels) with various sets of design parameters and a matrix composed of 20 x 20 pixels. The matrix is used to record and process pictures with a spatial resolution of 400 pixels. The design has been carried out using the 1.2 μm CMOS technology of the company AMS (Austria Micro Systems). This CMOS process offers two metal layers and two polysilicon layers.

Fig. 3 shows a microphotograph of the produced chip. The picture demonstrates the basic structure of the chip which has a size of 3.5×2.5 mm^2. The layout is divided into two separate structures. The left part contains various versions of single adaptive photoreceptors as well as some optoelectronic test structures. The right part shows the 400 pixel matrix arranged in 20 rows with 20 pixels each.

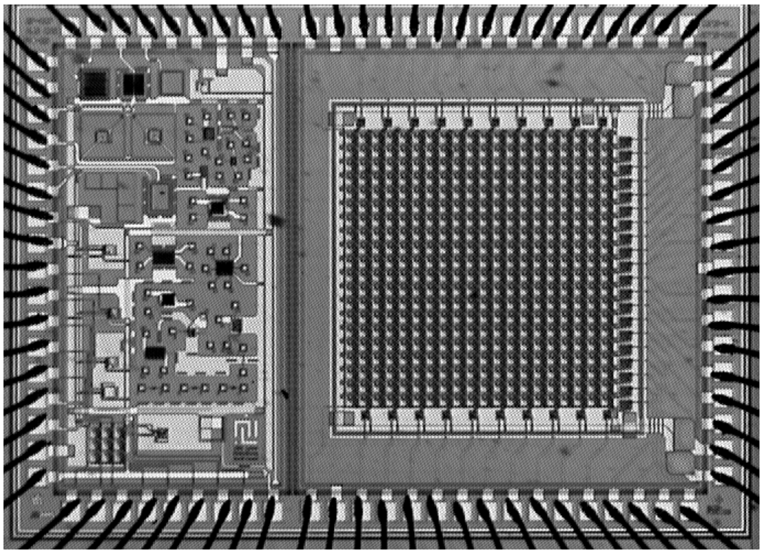

Figure 3: Microphotograph of the produced vision chip

The layout of a single adaptive pixels occupies a surface area of approximately 50×50 μm and is shown in Fig. 4. It is dominated by the capacitive divider formed by C_1 and C_2. The capacitors are build from two polysilicon layers. At the top edge of the pixel design the quadratic shape of the n^+-substrate photodiode can be seen. This type of diode is close to the surface of the silicon wafer. At the same time the diode extends far into the weakly doped substrate so that the diode exhibits a rather large quantum efficiency for visible light. The diode has been realised as a geometrical extension of the source area of the feedback transistor M_{fb} since source and drain of an n-MOS transistor are made of n^+-diffused material. The photodiode itself has a surface area of 15×15 μm^2. The remaining analog processing electronics is located at the right side of the pixel layout. Apart from the photodiode all other pn-junctions on the chip are also sensitive to light. For this reason the adaptive electronics has to be shielded. The second metal layer of the AMS process has been used for this purpose. The metal layer covers a major fraction of each pixel. The most critical part in terms of sensitivity to light is the adaptive element. For this reason it has been placed at maximum distance from the photodiode. This way only few scattered photons or diffusing charge carriers can reach the adaptive element.

The footprint of the chip is dominated by a matrix formed by 20×20 photoreceptors. The pixels in the matrix arrangement are somewhat modified compared to the standard pixel described before. Here the photodiode is surrounded by a strucure of contacts to the substrate forcing the substrate to ground potential. This way photocurrents travelling across the substrate can be carried away by the metal layer with very low impedance. Structures at large distance from the photodiode like the adaptive element are thus well protected against such currents. For the readout of the matrix pixel rows are activated via transistor switches set by external control signals. The readout proceeds columnwise through 20 readout amplifiers. All required readout circuitry like switching transistors, logic level converters and readout amplifiers is located on-chip. Digitisation is carried out